



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
N-		0.4Ω @ V <sub>GS</sub> = 10V	0.8A
Channel	30V	0.7Ω @ V <sub>GS</sub> = 4.5V	0.57A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- **Power Management Functions**
- DC-DC Converters

# **Features and Benefits**

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.027 grams (Approximate)

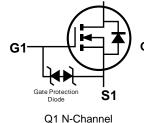


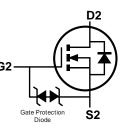


Top View

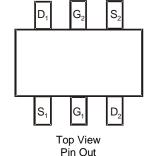
**SOT363** 







Q2 N-Channel

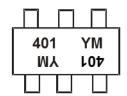


**Ordering Information** (Note 4)

	Part Number	Case	Packaging
	MN3401LDW-7	SOT363	3000/Tape & Reel
DI	MN3401LDW-13	SOT363	10000/Tape & Reel

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
  - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



401 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  or  $\underline{Y}$  = Year (ex:  $\overline{G}$  = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2	019	2020		2021	2022		2023	2024	ļ.	2025
Code	F		G	Н		I	J		K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	/ Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	30	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	0.8 0.6	А
Maximum Continuous Body Diode Forward Current (	I <sub>S</sub>	0.4	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	4	Α		

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	433	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	0.35	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	360	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

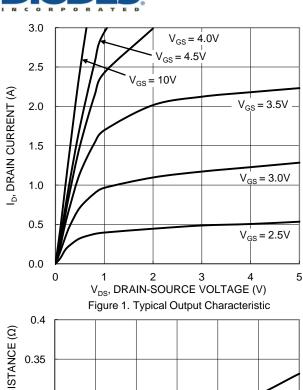
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

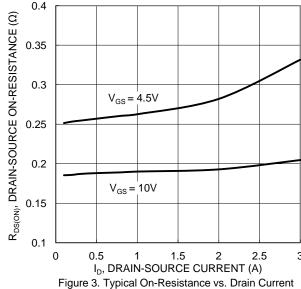
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Joyillboi	IVIIII	тур	IVIAA	Oilit	rest condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				•	•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	1.2	1.6	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	0.2	0.4	Ω	$V_{GS} = 10V, I_D = 0.59A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	0.3	0.7	Ω	$V_{GS} = 4.5V, I_D = 0.2A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	50	_	pF	V 45V V 6V	
Output Capacitance	C <sub>oss</sub>	_	12	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	10	_	pF	1 = 1.000112	
Gate Resistance	Rg	_	58	_	Ω	$V_{DS} = V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	0.5	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	1.2	_	nC	$V_{DS} = 10V, V_{GS} = 10V$	
Gate-Source Charge	Q <sub>gs</sub>	_	0.2	_	nC	I <sub>D</sub> = 250mA	
Gate-Drain Charge	$Q_{gd}$	_	0.1	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	3.3	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16.8	_	ns	$I_D = 100$ mA, $R_G = 25\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	13.8	_	ns		

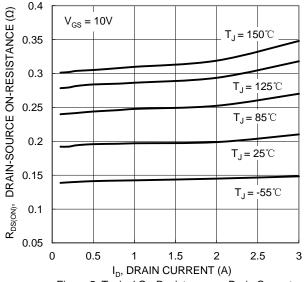
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.



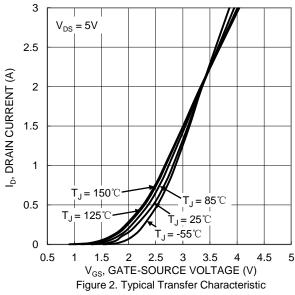


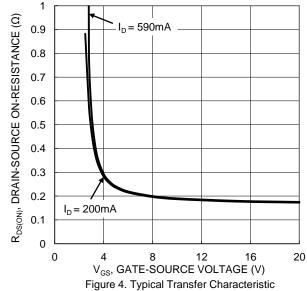




and Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





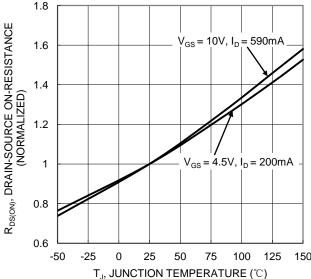
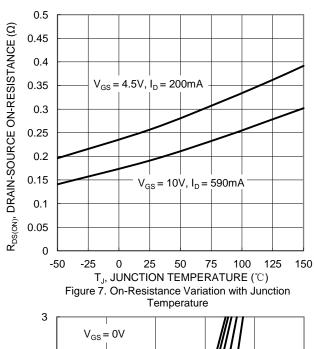
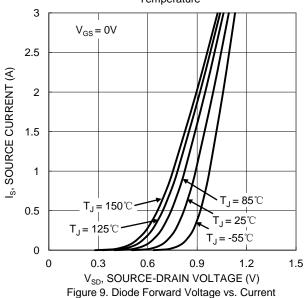


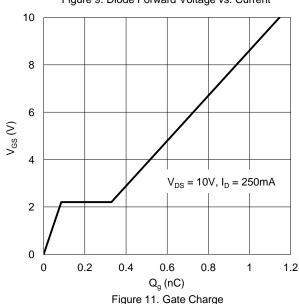
Figure 6. On-Resistance Variation with Junction Temperature

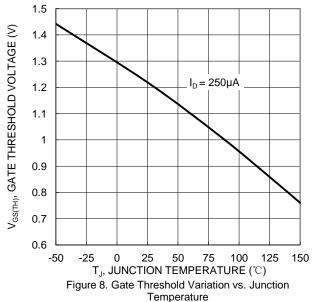


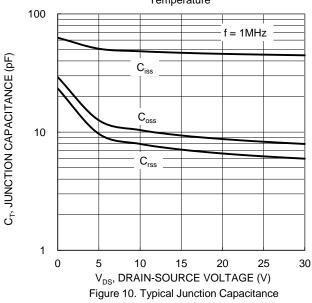


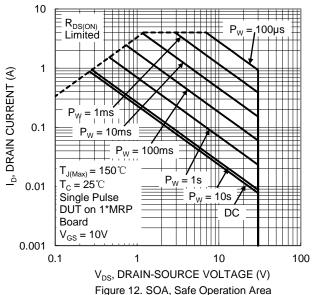














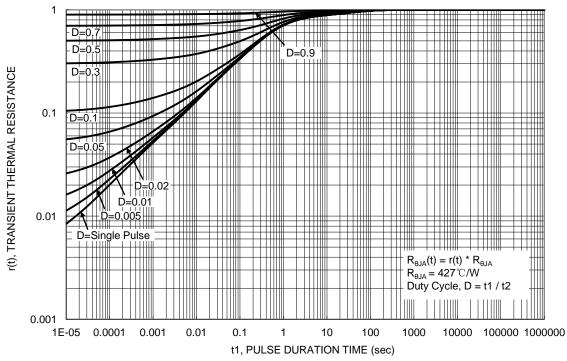


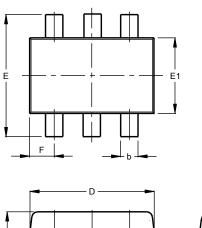
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



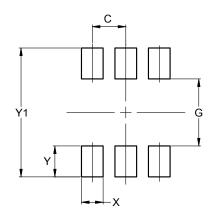
<b>-</b>	D		
A2			
	<u> </u>		
L Δ1	e —	†	<b>→</b> L <b>→</b> /

SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	.650 B	SC			
F	0.40	0.45	0.425			
١	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500



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